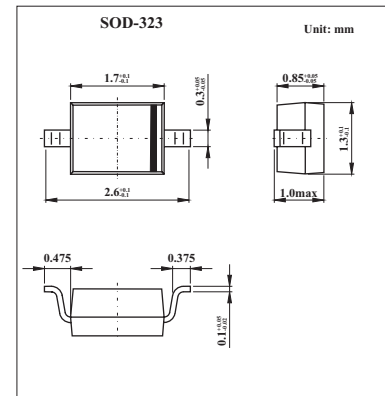


Silicon Epitaxial Planar Diode

1SV229

■ Features

- Ultra low series resistance: $r_s = 0.2 \Omega$ (typ.)
- Useful for small size set

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	15			V
Reverse Current	I_R	$V_R = 15\text{V}$			3	nA
Capacitance	C_{2V}	$f = 1\text{MHz}; V_R = 2\text{V}$	14	15	16	pF
	C_{10V}	$f = 1\text{MHz}; V_R = 10\text{V}$	5.5	6	6.5	
Capacitance Ratio	C_{2V}/C_{10V}		2	2.5		
Series Resistance	r_s	$V_R = 5\text{V}, f = 470\text{MHz}$		0.2	0.4	Ω

■ Marking

Marking	T8